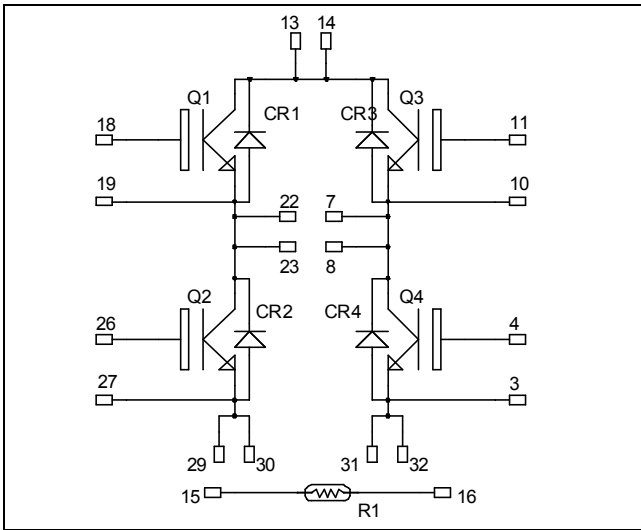


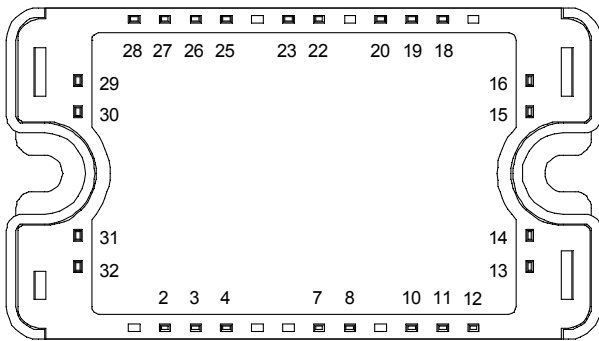
**Full - Bridge  
NPT & Trench + Field Stop<sup>®</sup> IGBT  
Power module**

**Trench & Field Stop<sup>®</sup> IGBT Q1, Q3:**  
 $V_{CES} = 600V$  ;  $I_C = 100A$  @  $T_c = 80^\circ C$

**Fast NPT IGBT Q2, Q4:**  
 $V_{CES} = 600V$  ;  $I_C = 90A$  @  $T_c = 80^\circ C$



Top switches : Trench + Field Stop IGBT<sup>®</sup>  
 Bottom switches : FAST NPT IGBT



All multiple inputs and outputs must be shorted together  
 13/14 ; 15/16 ; 26/27 ; 31/32

### Application

- Solar converter

### Features

- **Q2, Q4 FAST Non Punch Through (NPT) IGBT**
  - Switching frequency up to 100 kHz
  - RBSOA & SCSOA rated
  - Low tail current
- **Q1, Q3 Trench & Field Stop IGBT<sup>®</sup>**
  - Low voltage drop
  - Switching frequency up to 20 kHz
  - RBSOA & SCSOA rated
  - Low tail current

- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

### Benefits

- Optimized conduction & switching losses
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

## 1. Top switches

### 1.1 Top Trench + Field Stop IGBT<sup>®</sup> characteristics

#### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	600	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ\text{C}$	150 *
		$T_C = 80^\circ\text{C}$	100 *
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ\text{C}$	200
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	340
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ\text{C}$	200A @ 550V

\* Specification of IGBT device but output current must be limited to 75A to not exceed a delta of temperature greater than  $30^\circ\text{C}$  for the connectors.

#### Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$			250	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 100\text{A}$	$T_j = 25^\circ\text{C}$	1.5	1.9	V
			$T_j = 150^\circ\text{C}$	1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5\text{ mA}$	5.0	5.8	6.5	V
$I_{GES}$	Gate - Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA

#### Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0\text{V}$ $V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		6100		pF
$C_{oes}$	Output Capacitance			390		
$C_{res}$	Reverse Transfer Capacitance			190		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 100\text{A}$ $R_G = 3.3\Omega$		115		ns
$T_r$	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			225		
$T_f$	Fall Time			55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $150^\circ\text{C}$ ) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 100\text{A}$ $R_G = 3.3\Omega$		130		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			300		
$T_f$	Fall Time			70		
$E_{on}$	Turn on Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 100\text{A}$ $R_G = 3.3\Omega$	$T_j = 25^\circ\text{C}$	0.4		mJ
			$T_j = 150^\circ\text{C}$	0.875		
$E_{off}$	Turn off Energy	$I_C = 100\text{A}$ $R_G = 3.3\Omega$	$T_j = 25^\circ\text{C}$	2.5		mJ
			$T_j = 150^\circ\text{C}$	3.5		
$R_{thJC}$	Junction to Case Thermal resistance				0.44	$^\circ\text{C/W}$

## 1.2 Top fast diode characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R=600V$	$T_j = 25^\circ C$			100	$\mu A$
			$T_j = 125^\circ C$			500	
$I_F$	DC Forward Current		$T_c = 80^\circ C$		100		A
$V_F$	Diode Forward Voltage	$I_F = 100A$			1.6	2	V
		$I_F = 200A$			2		
		$I_F = 100A$	$T_j = 125^\circ C$		1.3		
$t_{rr}$	Reverse Recovery Time	$I_F = 100A$	$T_j = 25^\circ C$		160		ns
			$T_j = 125^\circ C$		220		
$Q_{rr}$	Reverse Recovery Charge	$V_R = 400V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ C$		290		nC
			$T_j = 125^\circ C$		1530		
$R_{thJC}$	Junction to Case Thermal resistance					0.55	$^\circ C/W$

## 2. Bottom switches

### 2.1 Bottom Fast NPT IGBT characteristics

#### Absolute maximum ratings

<i>Symbol</i>	<i>Parameter</i>	<i>Max ratings</i>		<i>Unit</i>
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
$I_C$	Continuous Collector Current	$T_c = 25^\circ C$	110	A
		$T_c = 80^\circ C$	90	
$I_{CM}$	Pulsed Collector Current	$T_c = 25^\circ C$	315	
$V_{GE}$	Gate - Emitter Voltage		$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	416	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	200A @ 600V	

#### Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $V_{CE} = 600V$	$T_j = 25^\circ C$			250	$\mu A$
			$T_j = 125^\circ C$			500	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 90A$	$T_j = 25^\circ C$		2.0	2.5	V
			$T_j = 125^\circ C$		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$		3		5	V
$I_{GES}$	Gate - Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				$\pm 150$	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C <sub>ies</sub>	Input Capacitance	V <sub>GE</sub> = 0V		4300		pF
C <sub>oes</sub>	Output Capacitance	V <sub>CE</sub> = 25V		470		
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1MHz		400		
Q <sub>g</sub>	Total gate Charge	V <sub>GE</sub> = 15V		330		nC
Q <sub>ge</sub>	Gate – Emitter Charge	V <sub>Bus</sub> = 300V		290		
Q <sub>gc</sub>	Gate – Collector Charge	I <sub>C</sub> = 90A		200		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C) V <sub>GE</sub> = 15V V <sub>Bus</sub> = 400V I <sub>C</sub> = 90A R <sub>G</sub> = 5 Ω		26		ns
T <sub>r</sub>	Rise Time			25		
T <sub>d(off)</sub>	Turn-off Delay Time			150		
T <sub>f</sub>	Fall Time			30		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (125°C) V <sub>GE</sub> = 15V V <sub>Bus</sub> = 400V I <sub>C</sub> = 90A R <sub>G</sub> = 5 Ω		26		ns
T <sub>r</sub>	Rise Time			25		
T <sub>d(off)</sub>	Turn-off Delay Time			170		
T <sub>f</sub>	Fall Time			40		
E <sub>on</sub>	Turn-on Switching Energy	V <sub>GE</sub> = 15V V <sub>Bus</sub> = 400V I <sub>C</sub> = 90A R <sub>G</sub> = 5 Ω	T <sub>j</sub> = 125°C	4.3		mJ
E <sub>off</sub>	Turn-off Switching Energy		T <sub>j</sub> = 125°C	3.5		
R <sub>thJC</sub>	Junction to Case Thermal resistance				0.3	°C/W

**2.2 Bottom diode characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage		600			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> = 600V	T <sub>j</sub> = 25°C		250	μA
			T <sub>j</sub> = 125°C		500	
I <sub>F</sub>	DC Forward Current		T <sub>c</sub> = 80°C	30		A
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 30A		1.6	1.8	V
		I <sub>F</sub> = 60A		1.9		
		I <sub>F</sub> = 30A	T <sub>j</sub> = 125°C	1.4		
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 30A V <sub>R</sub> = 400V di/dt = 200A/μs	T <sub>j</sub> = 25°C	85		ns
			T <sub>j</sub> = 125°C	160		
Q <sub>rr</sub>	Reverse Recovery Charge		T <sub>j</sub> = 25°C	130		nC
			T <sub>j</sub> = 125°C	700		
R <sub>thJC</sub>	Junction to Case Thermal resistance				1.2	°C/W

**3. Temperature sensor**

**NTC** (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

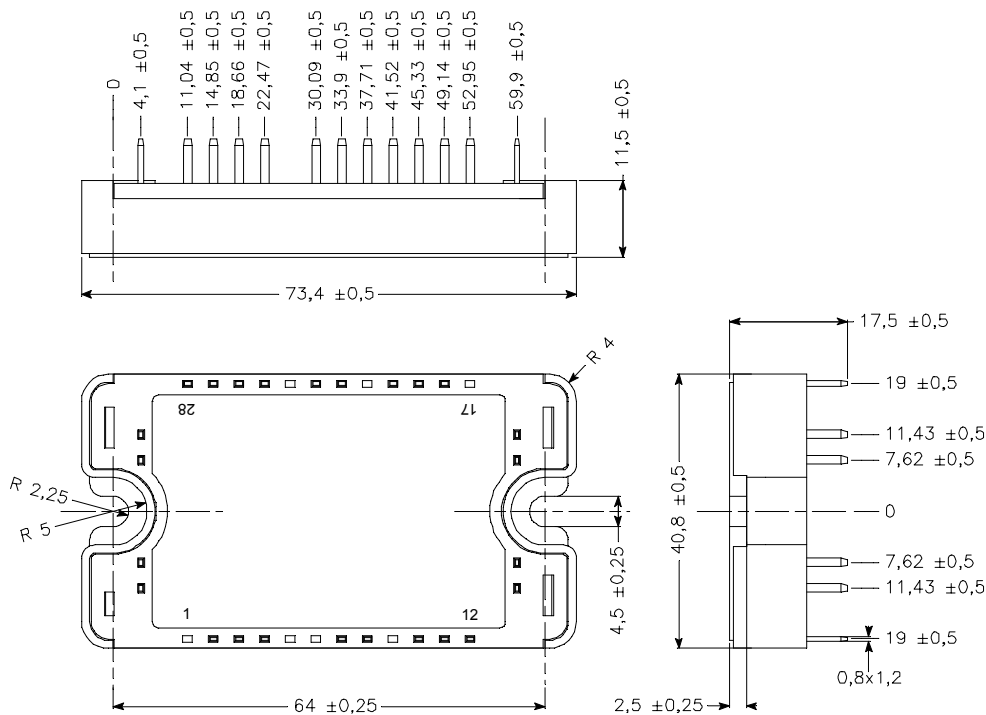
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

## 4. Package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150*	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

T<sub>j</sub>=175°C for Trench & Field Stop IGBT

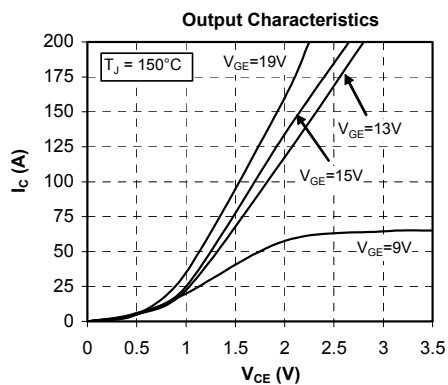
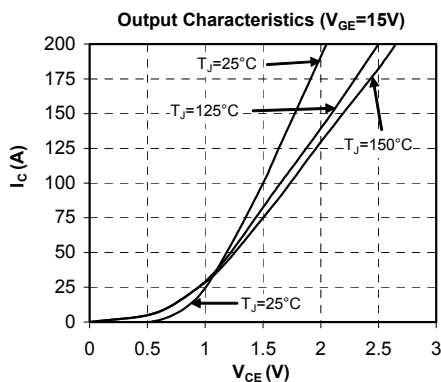
## 5. SP3 Package outline (dimensions in mm)

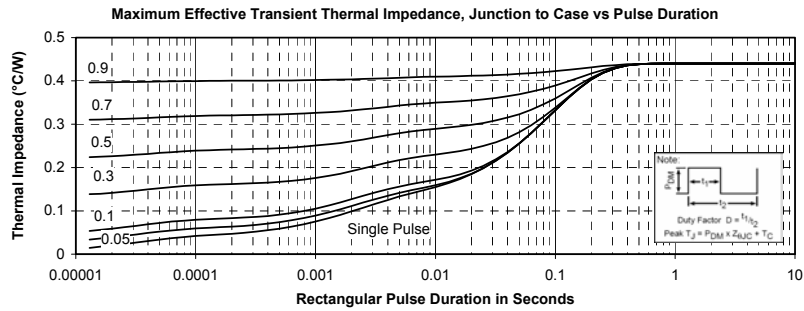
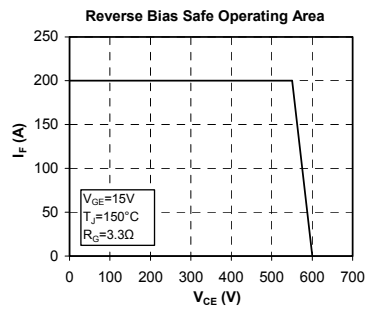
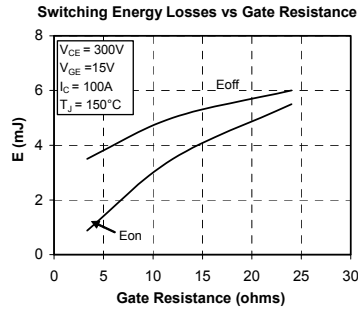
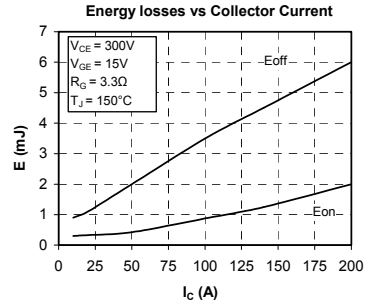
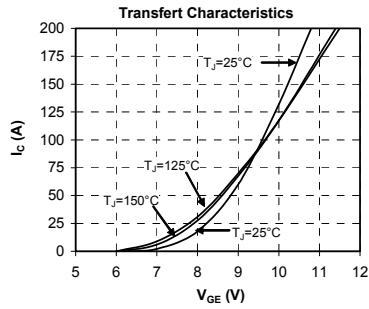


See application note 1901 - Mounting Instructions for SP3 Power Modules on [www.microsemi.com](http://www.microsemi.com)

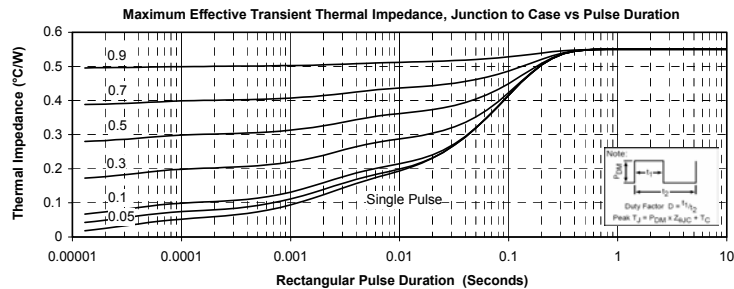
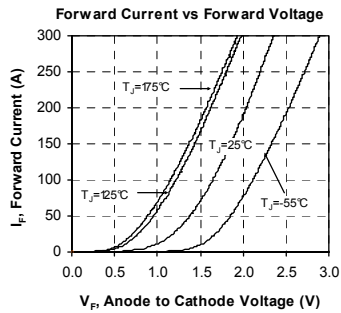
## 6. Top switches curves

### 6.1 Top Trench + Field Stop IGBT® typical performance curves



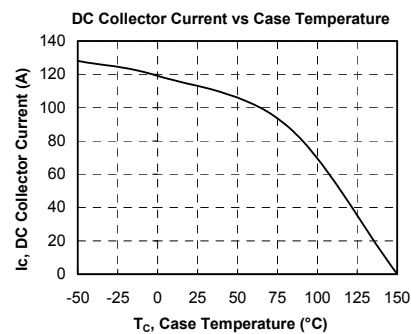
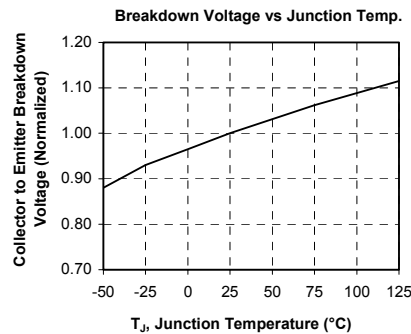
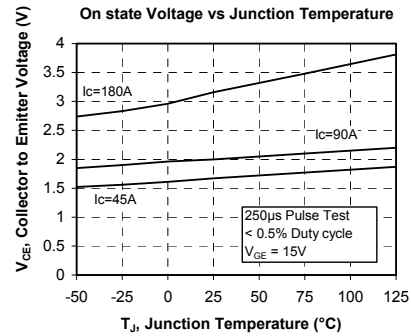
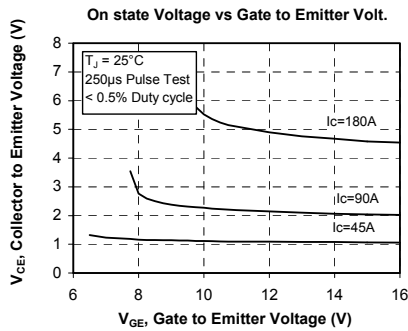
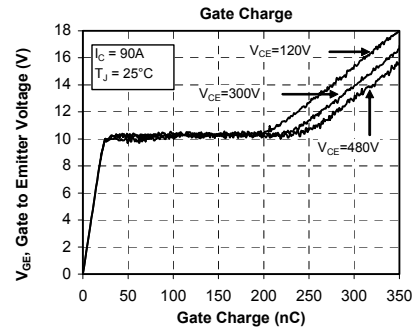
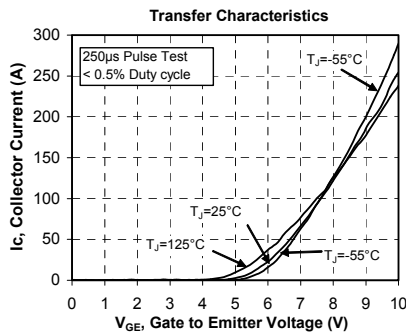
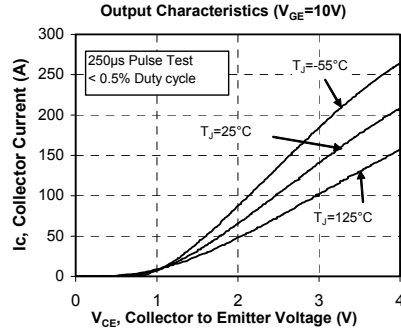
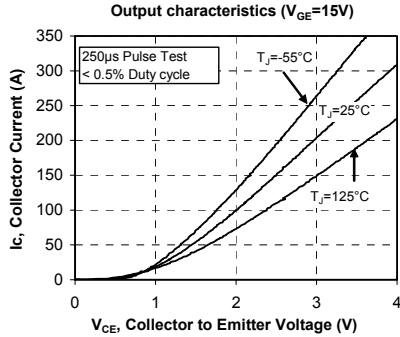


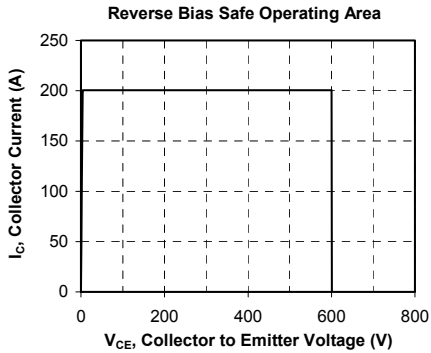
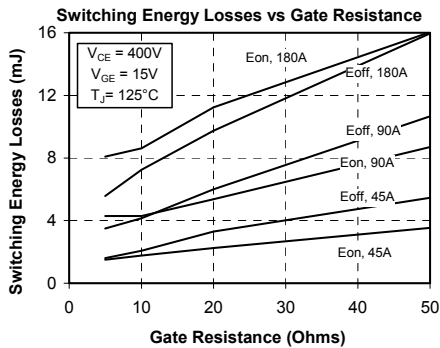
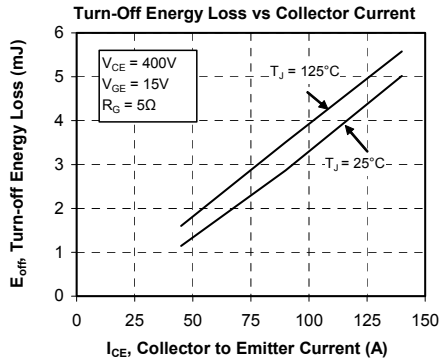
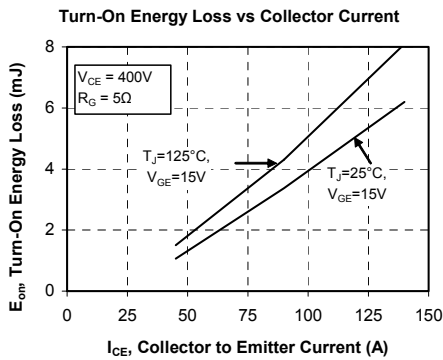
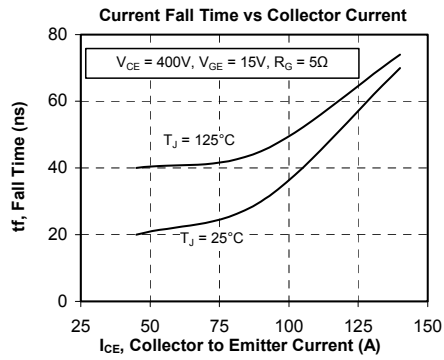
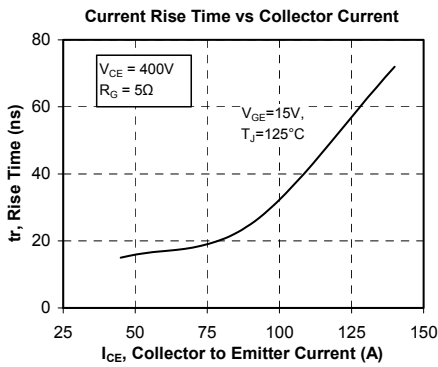
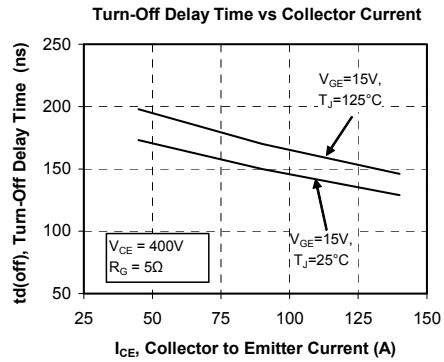
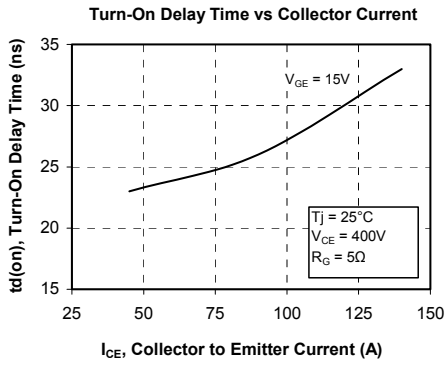
## 6.2 Top Fast diode typical performance curves



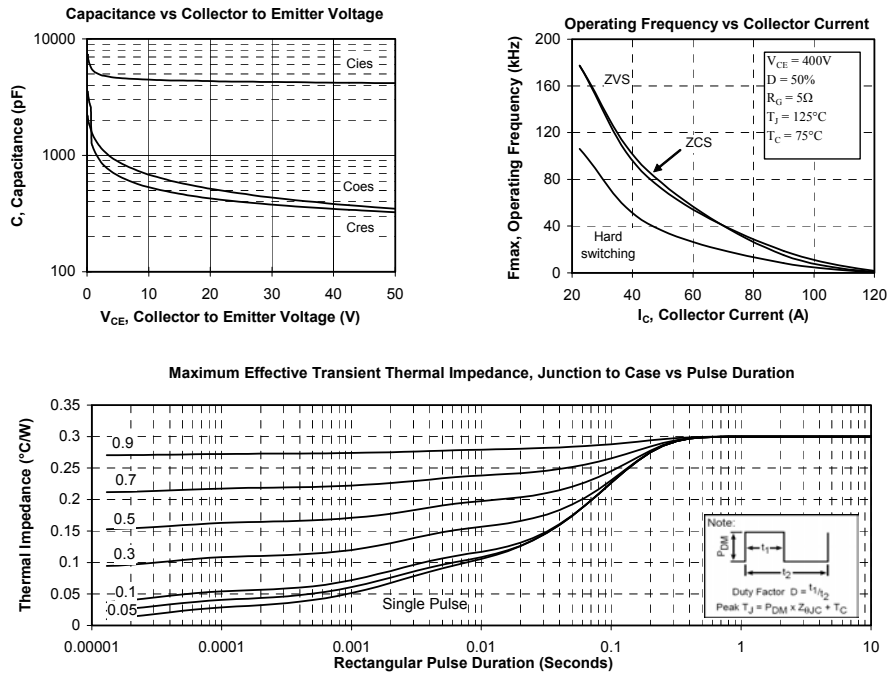
## 7. Bottom switches curves

### 7.1 Bottom fast NPT IGBT typical performance curves

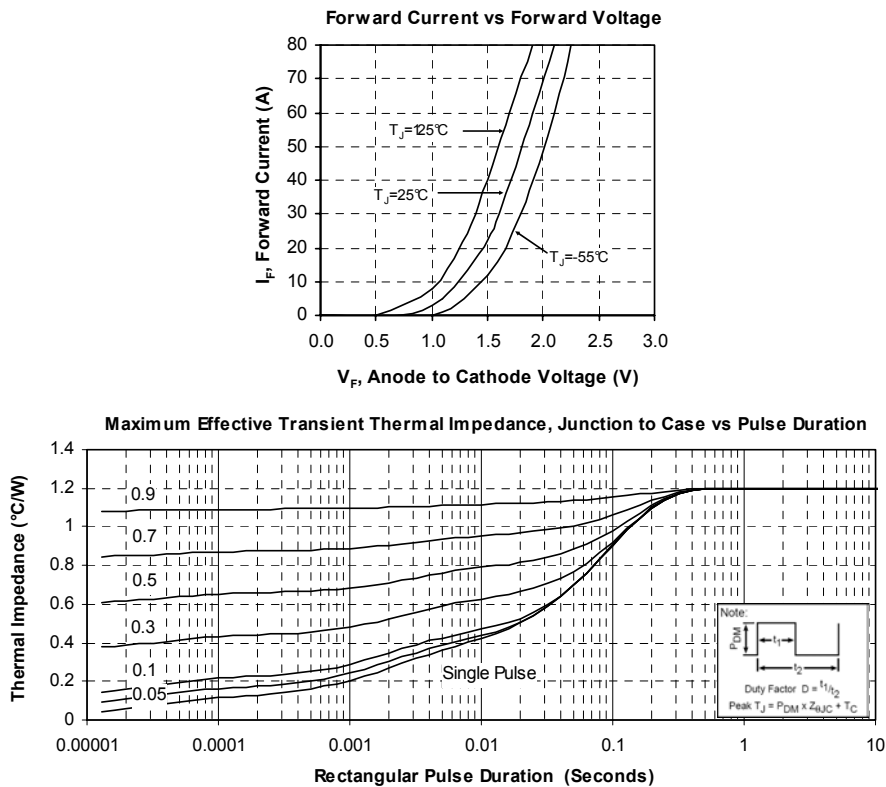








## 7.2 Bottom diode typical performance curves



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